

Mechanism of Efficient Adsorption of Na Atoms on Electron-Deficient Doped MoS₂ for Battery Electrodes

Yudong Pang¹, Zhansheng Lu^{1,†}, Shamraiz Hussain Talib,^{1,2} Xinyuan Li,¹ Mingyang Wang,¹ Xilin Zhang,¹ Zongxian Yang^{1,*}, and Ruqian Wu^{1,3,‡}

¹*School of Physics, Henan Normal University and Henan Key Laboratory of Photovoltaic Materials, Xinxiang, Henan 453007, People's Republic of China*

²*Department of Chemistry and Key Laboratory of Organic Optoelectronics & Molecular Engineering of Ministry of Education, Tsinghua University, Beijing 100084, People's Republic of China*

³*Department of Physics & Astronomy, University of California, Irvine, California 92697, USA*



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Due to the similarities in electrochemical and physicochemical properties of sodium and lithium, sodium-ion batteries are an attractive substitute for lithium-ion batteries. The selection of appropriate electrode materials for Na-ion batteries is an important step to achieve high stability and theoretical capacity. Here, the effects of heteroatom doping and charge variation on the ability of the MoS₂ substrate to capture Na ions are studied using first-principles calculations. The results show that the interaction between Na ions and the MoS₂ substrate is enhanced by electron deficiency or substituting a S atom with a dopant atom (X) with fewer valence electrons ($X = \text{B}, \text{Al}, \text{Ga}, \text{In}, \text{C}, \text{Si}, \text{Ge}, \text{Sn}, \text{N}, \text{P}, \text{As}, \text{Sb}$). In contrast, adding electrons to the MoS₂ substrate weakens its interaction with Na. We further analyze the diffusion barrier, open-circuit voltage, and theoretical capacity of hypothetical Na-ion batteries using doped $X\text{-MoS}_2$ ($X = \text{heteroatom}$) as electrode materials. We find that Al- or Si-doped MoS₂ can serve as good electrode materials for Na-ion batteries, with a high theoretical capacity that exceeds 700 mAh/g. This work provides practical guidance for the development of electrode materials of Na-ion batteries using two-dimensional materials.

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I. INTRODUCTION

Lithium-ion batteries (LIBs) are widely used in rechargeable automobiles, portable electronics, and energy storage due to their high power density as well as high energy density. However, due to the limited availability and unequal distribution of global lithium resources, the cost of LIBs constantly increases. In the meantime, they still have inherent technical issues, such as poor low-temperature performance and inadequate safety protection. Currently, interdisciplinary efforts are dedicated to developing batteries with metal ions that may offer low cost, environmental friendliness, and a high theoretical capacity. Among various potential candidates, sodium-ion batteries (SIBs) have attracted considerable attention, as they have very similar properties to Li-ion batteries but with lower cost and better safety [1–4]. Sodium is the next-smallest alkali metal and has a larger size than Li. A critical challenge for the development of Na-ion batteries is to find appropriate electrode and electrolyte materials that may

provide a large adsorption capacity, high mobility, and strong support for Na ions. To this end, the target materials must have an adequate grasp on Na ions, shallow barrier for their segregation, and strong structural stability.

Recently, many two-dimensional (2D) materials without and with modification by heteroatoms have been investigated as potential electrode materials for metal-ion batteries [5–16]. For example, graphene proves to be a superior electrode material for Li-ion batteries with high theoretical capacity [5,8,17,18]. However, the ionic radius of Na (1.06 Å) is larger than that of Li (0.76 Å), and the adsorption and diffusion kinetics of Na ions in graphene layers are somewhat limited [19–21]. To improve this scenario, Qiao *et al.* report that phosphorus doping in graphene may increase the interlayer spacing, and hence, enhance the adsorption and migration of Na ions between graphene layers [22]. They also report that the coupling between MoS₂ and nitrogen-doped graphene layers considerably enhances the adsorption capacity of Na ions [23]. Kavalsky and co-workers investigated the adsorption of Na ions on the blue phosphorus and found that this material had a high capacity for hosting alkali ions and high K and Na diffusivity [24]. Several types of heteroatom- (e.g., Si- [16], Ge- [9], and C- [12]) doped blue phosphorus are widely explored, and they

*yzx@htu.edu.cn

†zslu@htu.edu.cn

‡wur@uci.edu

are one of the top candidates for the design of battery materials. Recent studies further specify that pentagraphene as a substrate has a much higher theoretical capacity of Na or Li ions [25] compared with other 2D electrode materials. Cheng *et al.* report that B-doped pentagraphene may have an even higher theoretical capacity for Na- or Li-ion batteries than pristine pentagraphene [14]. Barik and Pal report that the presence of S and Mo vacancies may improve the Na-adsorption capacity and diffusion abilities of MoS₂ [26]. Feng *et al.* report that substituting Se with P in three-dimensional CoSe₂ enhances its theoretical Li capacity [27]. Ni *et al.* report that introducing oxygen vacancies leads to excellent performance of TiO₂ as an electrode material for Na-ion batteries [28]. From these prior studies, it is established that doped or defect materials are more suitable electrode materials for metal-ion batteries. In particular, this is a critical strategy to improve the performance of sodium-ion batteries by overcoming problems such as low capacity and poor initial Coulombic efficiency.

Here, we investigate how to engineer 2D MoS₂-based materials as electrodes in Na-ion batteries through systematic density-functional theory (DFT) calculations. Among popular 2D materials, MoS₂ is a van der Waals (vdW) type layered material [29] that is explored for a variety of applications, such as energy storage, optoelectronics, and spintronics. However, pure MoS₂ is not suitable as an electrode material for Na-ion batteries, as it has a large band gap, and hence, a weak interaction with Na [30]. To find out if heteroatoms can activate MoS₂, we perform systemic studies for the adsorption and segregation of Na on doped MoS₂ monolayer ($X\text{-MoS}_2$, $X = \text{B}, \text{Al}, \text{Ga}, \text{In}, \text{C}, \text{N}, \text{Si}, \text{Ge}, \text{Sn}, \text{N}, \text{P}, \text{As}, \text{Sb}, \text{O}, \text{Se}, \text{Te}, \text{F}, \text{Cl}, \text{Br}, \text{I}$). We first examine structural stability, ground-state electronic properties, and adsorption of Na ions of pure and N-doped MoS₂ (N-MoS₂) monolayer. To reveal the mechanisms, the charged systems of pure and N-doped MoS₂ are studied with electron extraction or injection. Finally, we investigate the important parameters for electrode materials, such as diffusion barrier, theoretical capacity, and open-circuit voltage, which primarily depend on the number of Na atoms on the substrate. We find that electron extraction from the MoS₂ substrate or substitution of a S atom of MoS₂ with a dopant that has fewer valence electrons increases the interaction between Na and MoS₂, resulting in a higher adsorption energy. We predict that the Al- or Si-MoS₂ systems can serve as good electrode materials for Na-ion batteries with a high theoretical capacity and high performance.

II. COMPUTATIONAL DETAILS

Using the Vienna *ab initio* simulation package [31,32] with the projected-augmented-wave approach [33], the first-principles calculations are performed based on the

spin-polarized DFT at the level of the generalized gradient approximation with the Perdew-Burke-Ernzerhof functional [34]. The vdW interaction is included using the DFT-D3 method [35,36]. The plane-wave cutoff is set as 500 eV, and the threshold convergence for energy is set at 1×10^{-5} eV. Structural relaxation is pursued until the maximum force is less than 0.02 eV Å⁻¹. To investigate Na adsorption on the $X\text{-MoS}_2$ substrates ($X = \text{B}, \text{Al}, \text{Ga}, \text{In}, \text{C}, \text{N}, \text{Si}, \text{Ge}, \text{Sn}, \text{N}, \text{P}, \text{As}, \text{Sb}, \text{O}, \text{Se}, \text{Te}, \text{F}, \text{Cl}, \text{Br}, \text{I}$), a single layer of MoS₂ with a 4 × 4 replication in the x - y plane and a vacuum layer of more than 15 Å along the z direction is used to mimic the substrate, as presented in Fig. 1(a). The Brillouin zone is sampled with a 3 × 3 × 1 Monkhorst-Pack k -point mesh for geometrical optimization and with a 5 × 5 × 1 k mesh for electronic structure calculations [37]. The charge transfer of doped systems is analyzed using Bader's quantum theory of atoms in molecules (QTAIM) [38,39]. The charge-accumulation and -depletion regions can be visualized through charge-density differences (CDDs = $\rho_{AB} - \rho_A - \rho_B$, with ρ_{AB} , ρ_A , and ρ_B representing the charge densities of combined and separated systems). Furthermore, the average adsorption energies (E_{ads}) for Na on the substrate are obtained from

$$E_{\text{ads}} = (\lambda E_{\text{Na}} + E_{\text{substrate}} - E_{\lambda\text{Na} + \text{substrate}})/\lambda. \quad (1)$$

Here, E_{Na} , $E_{\text{substrate}}$, and $E_{\lambda\text{Na} + \text{substrate}}$ represent the energy of a Na atom in the bulk Na metal, the energy of the substrate, and the energy of the substrate with λ Na adatoms, respectively. According to this definition, the greater the value of E_{ads} , the stronger the interaction between Na and the substrate. The climbing-image nudged elastic band (CINEB) method [40], with four mirror images inserted between the initial- and final-state structures, is used to search for the diffusion barriers. The energy and atomic force convergence threshold settings for CINEB are the same as those for structural optimization.

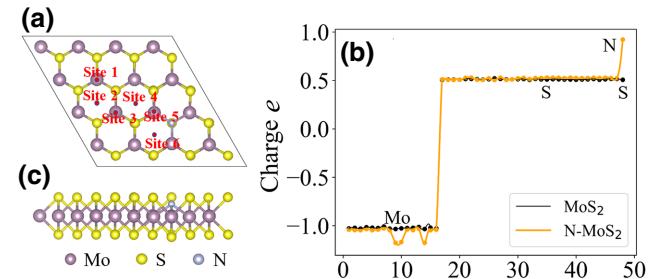


FIG. 1. (a),(b) Top and side views of N-MoS₂ substrate, with different adsorption sites (red dots) for the Na atom (site 1–site 6). (c) Bader charges of MoS₂ and N-MoS₂. Positive value represents gain of electrons. Numbers on the x axis show the labels (1–16 for Mo and 17–48 for S and N) of the atoms in our model.

The open-circuit voltage (V_{OC}) is calculated from E_{ads} by

$$V_{OC} = E_{ads}/e, \quad (2)$$

where e is the charge of an electron. The theoretical storage capacity (C) is calculated by

$$C = xF/M_{\text{substrate}}, \quad (3)$$

where x represents the maximum number of adsorbed Na atoms on the substrate, F is the Faraday constant ($F = 26.8 \text{ Ah/mol}$), and $M_{\text{substrate}}$ is the molecular mass of the substrate.

III. RESULTS AND DISCUSSION

A. The geometric and electronic properties of MoS₂ and N-MoS₂

Since the MoS₂ structure of the 2H phase is more stable than that of the 1T phase, here we choose the 2H-phase structure as the model for research. In this work, the 2H-phase MoS₂ monolayer is chosen as the template and different heteroatoms (B, Al, Ga, In, C, N, Si, Ge, Sn, N, P, As, Sb, O, Se, Te, F, Cl, Br, I) are used as dopants for substituting the S atoms. Among them, N-MoS₂ is studied experimentally and it is found that the Mo—N bonds are strong in N-MoS₂ [23]. Accordingly, we first study the geometric and electronic properties of N-MoS₂ and compared them with those of the pristine MoS₂ monolayer. The top and side views of the optimized configuration of N-MoS₂ are presented in Figs. 1(a) and 1(b). It is found that, in the optimized structure of N-MoS₂, the N—Mo bond length (2.04 Å) is considerably shorter than the S—Mo bond (2.41 Å), signifying that there is a strong interaction between the N and Mo. Figure 1(c) depicts the charge-distribution comparison between the MoS₂ and N-MoS₂ substrates. The Bader charge analysis further confirms the strong interaction between N and MoS₂. In the pristine MoS₂ monolayer, each Mo atom transfers 1 | e | and each S atom gains 0.5 | e |. In N-MoS₂, the Mo atoms nearest to N donate more electrons (approximately 1.2 | e |) to the N atom, and the N atom gains 0.9 | e | from its neighbors [see Fig. 1(c)]. The larger electronegativity of N (3.04) compared with that of S (2.58) explains this extra electron gain and implies stronger binding between N and Mo than that between S and Mo.

TABLE I. Adsorption energies (E_{ads}) and Na-substrate average distance (d_{av}) for Na ions at different adsorption sites over the MoS₂ and N-MoS₂ substrates.

	N-MoS ₂						Pure
	Site 1	Site 2	Site 3	Site 4	Site 5	Site 6	MoS ₂
E_{ads} (eV)	1.467	1.453	1.517	1.503	2.120	2.118	0.126
d_{av} (Å)	2.73	2.75	2.73	2.73	2.23	2.23	2.76

B. The adsorption of Na on MoS₂ and N-MoS₂

Next, we investigate the adsorption of Na over the N-MoS₂ substrate. The structure of the N-MoS₂ substrate has low symmetry and Na ions are likely to adsorb at six different sites [see Fig. 1(a)]. There are two different kinds of adsorption sites. Site 1, site 3, and site 5 are located directly above the Mo atom, while site 2, site 4, and site 6 are located in the hollow sites of MoS₂. Their positions and distances relative to dopant X can be seen from the top view of the structure. The calculated adsorption energies and the Na-substrate average distances are listed in Table I, along with corresponding values for Na on pristine MoS₂. As expected, the absorption of Na on pure MoS₂ is very weak, with an adsorption energy of only 0.13 eV. In contrast, the adsorption energies of Na over the N-MoS₂ substrate at different adsorption sites are consistently high, 1.45 to 2.12 eV. The significant increase in adsorption energy can be attributed to the change of local chemistry of N-MoS₂. As shown in Table I, stable adsorption sites for Na are around the top of Mo (sites 5 and 6) near N, and the adsorption energy is as high as 2.12 eV. Obviously, the ability of MoS₂ to host Na atoms is significantly improved by N doping. Furthermore, we find that strong adsorption of Na correlates well with the average distance between the Na ion and N-MoS₂ substrate [see Table I]. To further explore the origin of the strong interaction between Na and the N-MoS₂ substrate, Figs. 2(ai) and 2(aii) gives the Bader charges for Na/N-MoS₂ in all possible adsorption configurations. It is clear that the Na atom close to the doped N atom site loses more electrons than those at the other adsorption sites. We may conclude that electron transfer from Na to N is primarily responsible for the enhanced interaction between Na and N-MoS₂.

C. The mechanism for the enhancement of Na adsorption on N-MoS₂

To further explore the adsorption properties of Na over the N-MoS₂ substrate, the CDDs are presented in Figs. 2(b) and 2(g). These results show a substantial charge reduction around the Na atom at site 5 and site 6, and charge accumulation around the N atom nearby, in good correspondence with the Bader charge analysis. Since N has one less valence electron than S, doping N into MoS₂ generates an electron-deficient system, and hence, N-MoS₂

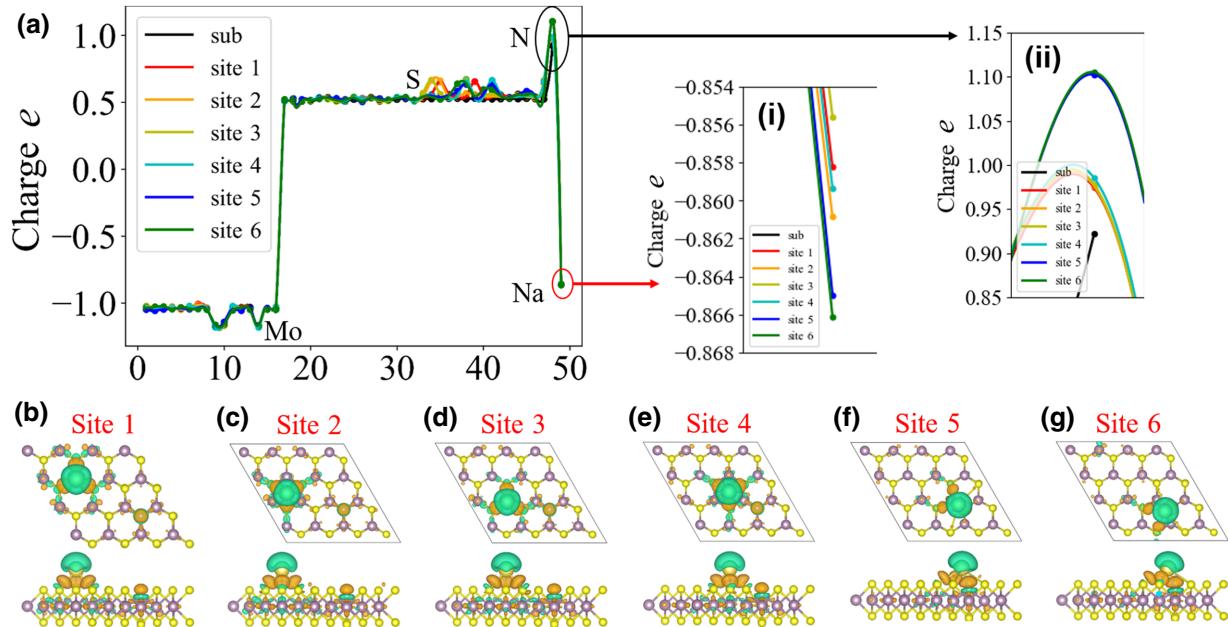


FIG. 2. (a) Bader charge analysis of Na atom adsorbed at different adsorption sites on the N-MoS₂ substrate. Numbers on the x axis show the labels of the atoms in the model. (b)–(g) CDD analysis of Na adsorbed at different sites on the N-MoS₂ substrate. For contour plots, the green region represents charge depletion, and the orange region represents charge accumulation. Isosurface value of the CDDs is $0.002 \text{ e}/\text{\AA}^3$.

may easily take the valence electron from Na. In this section, we analyze the effect of charge deficiency on the adsorption of Na on MoS₂ and N-MoS₂ substrates by extracting (injecting) electrons from (into) both systems. We first extract an electron from the pristine MoS₂ monolayer and observe its effect on the Na-adsorption

ability. Figure 3(a) shows the Bader charge distribution of MoS₂ before and after electron extraction. After extracting an electron from the MoS₂ substrate, the Bader charges of the S atoms are slightly reduced. Figures 3(b), 3(c), 7(a), and 7(b) (Appendix) illustrate the Bader charges and CDDs of Na/MoS₂ with or without electron extraction.

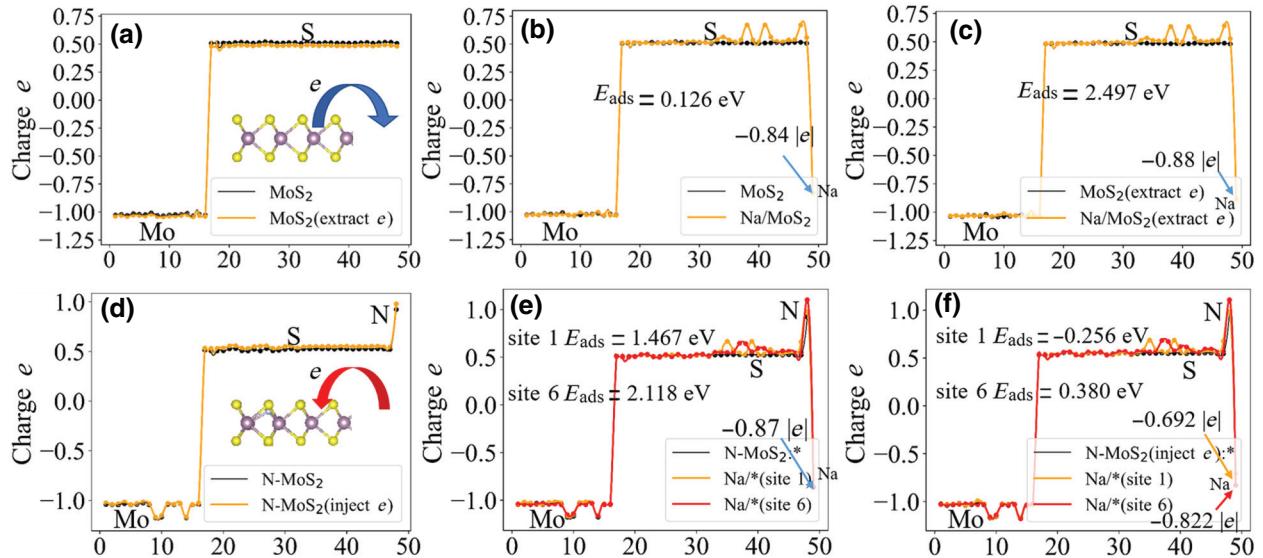


FIG. 3. (a) Bader charge analysis for electrons extracted from the pure MoS₂ substrate. (b) Charge variation of Na/MoS₂. (c) Charge variation of Na/MoS₂ (extract e). (d) Electrons injected in the N-MoS₂ substrate. (e) Charge variation of Na/N-MoS₂. (f) Charge variation of Na/N-MoS₂ (inject e). Numbers on the x axis show the labels of the atoms in the model.

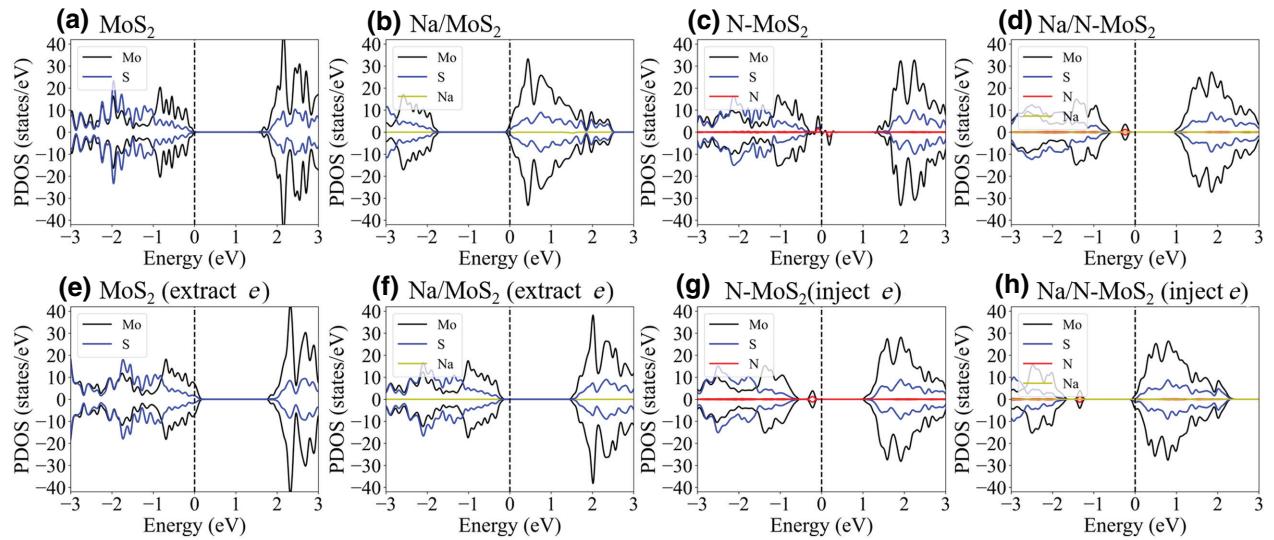


FIG. 4. PDOS for Na adsorption on the MoS₂ and N-MoS₂ substrates. (a) PDOS of the MoS₂ system. (b) PDOS of Na adsorption on the MoS₂ system. (c) PDOS of the N-MoS₂ substrate. (d) PDOS of Na adsorption on the N-MoS₂ substrate. (e) PDOS of the MoS₂ (extract *e*) substrate. (f) PDOS of Na adsorption on the MoS₂(extract *e*) substrate. (g) PDOS of the N-MoS₂ (inject *e*) substrate. (h) PDOS of Na adsorption on the N-MoS₂ (inject *e*) substrate.

The results show that the Na atom loses additional 0.04 |*e*| due to extraction of an electron from Na/MoS₂. Interestingly, the adsorption energy of Na becomes 2.50 eV, around 19 times more than that on MoS₂ without electron extraction. This evolution is in accordance with the expectation that the electron-deficient MoS₂ substrate enhances the interaction between Na and MoS₂.

On the other hand, we may expect that a dopant introducing additional electrons into the system weakens Na adsorption. To check this conjecture, we inject an electron into the N-MoS₂ system and observe the interaction between Na and the N-MoS₂ substrate. Figure 3(d) clearly shows that, when an electron is injected into the N-MoS₂ system, the charge distribution of the N-MoS₂ (injected *e*) system is slightly changed compared with that of N-MoS₂, e.g., the numbers of electrons that S and N atoms gain slightly increase. Figures 3(e), 3(f), and 7(c)–7(f) (Appendix) show the Bader charges and CDDs of Na on the N-MoS₂ substrate with and without electron injection. When Na is adsorbed at site 1 (site 6) on the N-MoS₂ (inject *e*) substrate, the Bader charge analysis shows that the Na atom loses fewer electrons to the substrate by 0.05 |*e*| (0.17 |*e*|) compared with that on N-MoS₂ without electron injection. The adsorption energy of Na at site 6 on the N-MoS₂ (inject *e*) substrate is reduced to 0.38 eV, approximately 6 times less than that on the N-MoS₂ substrate (2.12 eV). The negative adsorption energy of Na at site 1, which is far away from N, means that Na cannot be stably adsorbed. According to the analyses above, we may conclude that the electron-deficient MoS₂-based systems (e.g., N-MoS₂) are beneficial for Na adsorption,

while dopants with excess valence electrons weaken Na adsorption.

Figure 4(a) shows the partial density of states (PDOS) of the pure MoS₂ substrate, where the Fermi level is in the forbidden band and the band gap is about 1.7 eV. As confirmed in Fig. 4(b), it is clear that the PDOS peak of the Na/MoS₂ system is downshifted due to Na adsorption. Because the Fermi level is in the forbidden band, the electron transferred from Na needs to occupy states at the conduction-band minimum, a status that is unfavorable. In addition, we also present the PDOS for N-MoS₂ in Fig. 4(c) and PDOS for Na adsorption on the N-MoS₂ substrate in Fig. 4(d). In Fig. 4(c), the doped N atom on MoS₂ has empty half-filled orbitals near the Fermi level. When Na is adsorbed on the N-MoS₂ substrate, the electron transfers from Na to the empty orbitals near the Fermi level, which is clearly seen in Fig. 4(d). It is noteworthy that electron transfer from Na to N-MoS₂ is much easier than that to pure MoS₂, resulting in a stronger interaction between Na and N-MoS₂.

To further clarify why Na is more strongly adsorbed on N-MoS₂, the PDOS of the systems with Na adsorbed on the charged MoS₂ and N-MoS₂ substrates are analyzed. It is noteworthy that, when an electron is extracted from the MoS₂ system, the Fermi level moves to the left, leaving an empty state near the Fermi level, as shown in Fig. 4(e). When the Na atom is adsorbed on the MoS₂ (extract *e*) substrate, the electron from Na may easily fill this empty state, as shown in Fig. 4(f). Likewise, when electrons are injected into N-MoS₂, the empty band near the Fermi level is completely filled [see Fig. 4(g)]. The electron from Na

hence has to occupy the high-energy empty states in the conduction band [see Fig. 4(h)].

D. Potential efficient MoS₂-based electrode materials for Na-ion batteries

Based on the analyses above, systems with empty states near the Fermi level are suitable for the adsorption of Na. This can be further confirmed by examining the properties of MoS₂ with different heteroatoms (X), from groups IIIA to VIIA ($X = B, Al, Ga, In, C, Si, Ge, Sn, N, P, As, Sb, O, Se, Te, F, Cl, Br, I$). The stability of the X-MoS₂ structures is discussed in the Appendix. As shown in Fig. 8 (Appendix), the adsorption energies of Na on the X-MoS₂ substrate with electron-deficient dopants ($X = B, Al, Ga, In, C, Si, Ge, Sn, N, P, As, Sb$) are enhanced [see Table II in the Appendix], while the adsorption energies of Na on X-MoS₂ for the isoelectronic dopants ($X = O, Se, Te$) are very close to that on pristine MoS₂. These results stem from the reasons discussed above, as similar behavior can be seen from the PDOS of Na/X-MoS₂ in Fig. 9 (Appendix). In contrast, it is seen that the X-MoS₂ substrates with electron-rich group-VIIA dopants ($X = F, Cl, Br$, and I) have a moderate adsorption strength to Na. However, our test calculations show that the relaxed structures shown in Fig. 10 (Appendix) indicate that the strong interaction between the dopants of F, Cl, Br, and I with Na result in the precipitation of these dopant atoms from the dopant sites on the MoS₂ substrate upon adsorption of multiple Na ions with a concentration of Na:MoS₂ of 1:1. This is extremely disadvantageous for the stability of the structure and is not the case for MoS₂ doped with other dopant atoms, as also shown in Fig. 10 (Appendix). Therefore, electron-rich group-VIIA elements are not appropriate dopants in the MoS₂ substrate for the development of electrode materials for Na-ion batteries.

Generally, the diffusion barrier of Na on the substrate is another most important parameter for the performance of electrode materials. The diffusion properties of Na on the heteroatom-doped X-MoS₂ systems are closely associated with their rate capability, and small diffusion barriers are obligatory for electrode materials. Based on the adsorption sites and structural symmetry, the two most possible diffusion paths (path 1, site 1 → site 2 → site 3 → site 4; path 2, site 1 → site 4) are selected to study Na diffusion on pure MoS₂ or on the clean part (the region far away from the doped X atoms) of doped X-MoS₂. Na diffusion near the dopant is selected to study the effect of the dopant on Na diffusion (path 3, site 4 → site 5). The calculated energy profiles and optimized structures for Na-atom diffusion on the N-MoS₂ substrate are presented in Figs. 5, 11, and 12 (Appendix). Figures 5(a) and 5(b) show the Na diffusion routes via path 1 and path 2 on the clean part of N-MoS₂, from which we find diffusion barriers of about 0.1 eV (0.4 eV) via path 1 (path 2) [see Figs. 5(c) and 5(d)], with

path 1 being kinetically more favorable. This result is similar to the diffusion of Na on the MoS₂ substrate, see Fig. 11 (Appendix). However, Na diffusion near the N dopant (path 3, site 5 → site 4) is required to overcome a barrier of 0.68 eV [see Fig. 12(c) in the Appendix]. Although the N-MoS₂ substrate improves the adsorption strength of Na on the substrate, it decreases the diffusion ability of Na near the stable site near the doping site. In addition, the diffusion of Na on the other heteroatom systems is also studied in this work, and the computed geometries and potential-energy profiles are summarized in Fig. 13 (Appendix) and Table III (Appendix). By comparing Na diffusion on the N-MoS₂ substrate, we find that Na diffusion on the X-MoS₂ ($X = C, P, Ge, Ga, B$) substrates has similar properties to that on the N-MoS₂ substrate. In these systems, the Na ions can easily diffuse to the site close to the dopant (e.g., from site 4 to site 5) with a small diffusion barrier. However, inverse diffusion away from the doping site (from site 5 to site 4) has larger energy barriers (>0.2 eV). Thus, these systems are not appropriate as electrode materials. In contrast, the diffusion barriers of Na from site 4 to site 5 and from site 5 to site 4 on the X-MoS₂ ($X = As, Si, Al$) substrates are relatively close and small, with diffusion barriers less than 0.1 eV. Obviously, if the X-MoS₂ substrate makes the adsorption strength of Na at each position on the substrate surface more even, then the potential barriers of forward and backward diffusion of Na on these materials are similar, which makes the insertion and removal of Na easier. Therefore, these systems have a superb ion-diffusion ability and would be suitable electrode materials.

Additional important parameters for electrode materials are the theoretical capacity and open-circuit voltage, which primarily depend upon the amount of Na atoms adsorbed on the substrates. The calculated step diagrams (C-V diagram) of theoretical capacity and open-circuit voltage

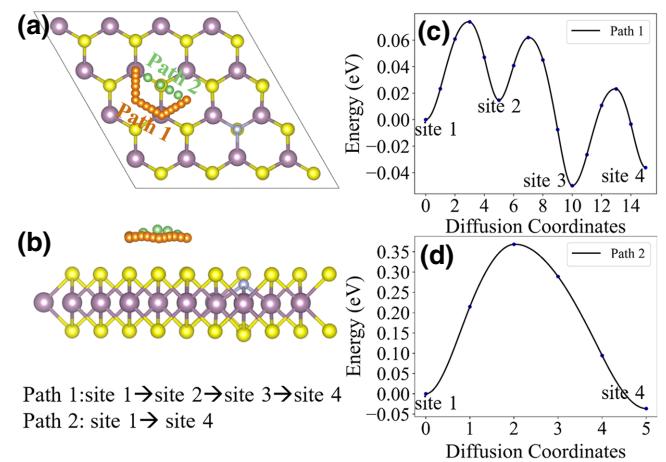


FIG. 5. (a),(b) Top and side views of Na-diffusion paths on the N-MoS₂ substrate. (c) Energy profile for Na diffusion via path 1. (d) Energy profile for Na diffusion via path 2.

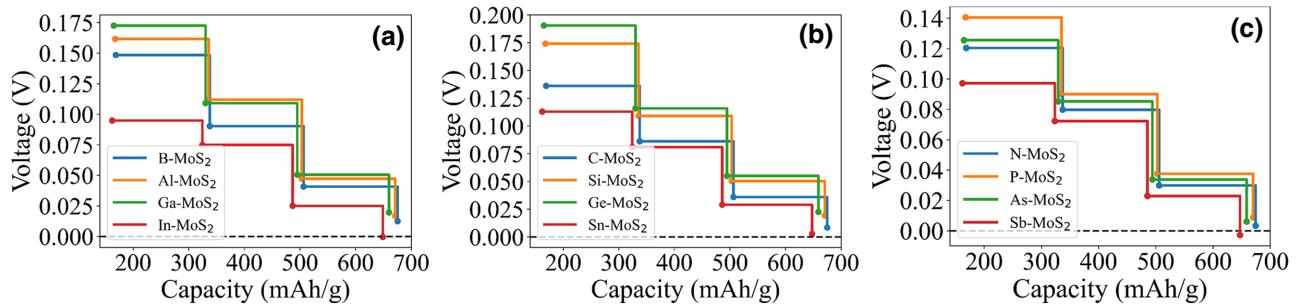


FIG. 6. Step diagrams of theoretical capacity (C) and average open-circuit voltage (V_{OC}) of multiple Na adsorption on the X -MoS₂ substrates (X = heteroatoms). (a) C - V diagram of group-III A-element-doped MoS₂. (b) C - V diagram of group-IV A-element-doped MoS₂. (c) C - V diagram of group-V A-element-doped MoS₂.

of the Na atom adsorbed on the X -MoS₂ substrates are presented in Fig. 6. Like MoS₂, X -MoS₂ (X = O, Se, and Te) has a weak adsorption ability for Na atoms, and thus, they will have poor theoretical capacities. Therefore, the MoS₂ substrates doped with the group-VIA element are not further discussed. Figure 6 depicts the relationship between theoretical capacity and open-circuit voltage for the doped substrates of X -MoS₂ with dopants from groups IIIA to VA. As seen in Fig. 6(a), for the X -MoS₂ systems with the group-III A-dopant elements (B, Al, Ga, In), the theoretical capacity shows a good relationship with the open-circuit voltage, i.e., with the increase in theoretical capacity, the open-circuit voltage decreases. The In-MoS₂ system shows a minimum open-circuit voltage of 0 V; the maximum theoretical capacity is about 650 mAh/g. However, other doped systems of X -MoS₂ (X = B, Al, Ga) show a maximum theoretical capacity of more than 700 mAh/g. Similarly, with the group-IV A (C, Si, Ge, Sn) and -VA (N, P, As, Sb) dopants, X -MoS₂ substrates show similar trends to those with the group-III A dopants. As presented in Figs. 6(b) and 6(c), compared with other elements in the same group, the maximum theoretical capacity of X -MoS₂ (X = Si, Ge) exceeds 700 mAh/g. Therefore, it can be seen that doped systems of X -MoS₂ (X = B, Al, Ga, Si, Ge) are very promising high-capacity electrode materials. Considering the previous results that the X -MoS₂ (X = As, Si, Al) systems have smaller diffusion barriers, we predict that X -MoS₂ (X = Al, Si) might be good candidates as electrode materials for SIBs with a high rate performance and high theoretical capacity [as shown in Fig. 14 in the Appendix].

IV. CONCLUSIONS

Based on first-principles calculations, we explore the feasibility of developing 2D MoS₂ substrates as electrode materials for Na-ion batteries. The effect of heteroatom

doping, charge variation, and the ability to adsorb Na ions are studied systematically. It is found that the MoS₂-based systems with suitable empty states near the Fermi level may facilitate the adsorption of Na, which can be tuned by introducing electron-deficient dopants (e.g., group-III A, -IV A, and -VA elements) into MoS₂.

In addition, the diffusion barrier, theoretical capacity, and open-circuit voltage are examined by doping heteroatoms (X = B, Al, Ga, In, C, Si, Ge, Sn, N, P, As, Sb, O, Se, Te, F, Cl, Br, I) into the MoS₂ substrate. It is found that doping can create active centers on the MoS₂ substrate, and Na atoms may easily diffuse to the active center. From the potential diffusion profile of Na on X -MoS₂, we find that the Si-, As-, and Al-doped systems are highly promising electrode materials with the lowest diffusion barrier (~ 0.1 eV) compared with the other doped systems. The theoretical capacity and open-circuit voltage studies indicate that the B-, Al-, Ga-, Si-, and Ge-doped MoS₂ substrate are highly favorable electrode materials for Na-ion batteries. As a result, we predict that the Al- and Si-MoS₂ systems can serve as electrode materials for Na-ion batteries, with a high theoretical capacity and high rate performance. These results provide valuable suggestions for experimentalists to design more efficient Na-ion-battery electrode materials with extremely high theoretical capacity.

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APPENDIX: THE STABILITY OF THE $X\text{-MoS}_2$ STRUCTURES

There are many reports in the literature on the formation energy of the $X\text{-MoS}_2$ structure and the heteroatoms used in this work. For example, the substitution of Al [41–44], B [44,45], C [46], Si [42,43,45], Ge [47], N [44,48–51], P [42–44,50–52], As [51], O [53], Se [54], Te [55], F [51], Cl [51,56], Br [51], and I [51] atoms for one S atom of MoS_2 substrates has been studied from various aspects, and these reports also discuss their stability separately. Among the dopant atoms considered in the present research, only four candidates (Ga, In, Sn, Sb) are not reported.

Since MoS_2 materials may easily generate S vacancies in the synthesis process, according to the literature [57–59], the binding energy of the dopant atoms at the S vacancies (defined as $E_{\text{bind}} = E_X + E_{\text{vac - MoS}_2} - E_{X - \text{MoS}_2}$) in MoS_2 is usually used to judge the stability of the dopant atoms. The calculated binding energies shown in Table IV indicate that

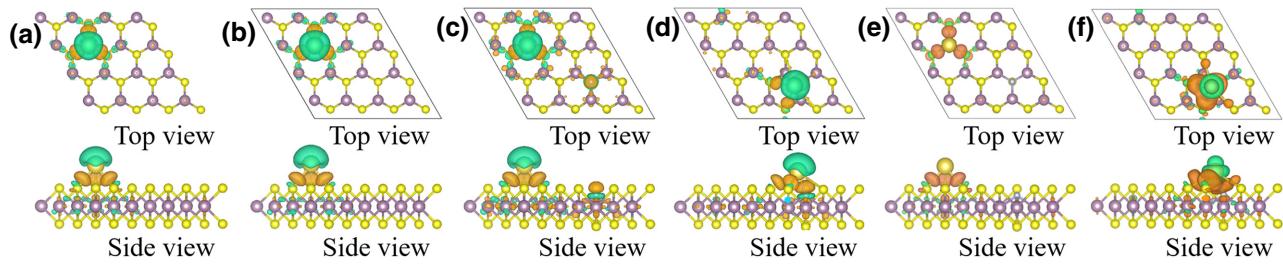


FIG. 7. (a),(b) CDDs of Na atom adsorbed at site 1 on the MoS_2 and MoS_2 (extract e) substrates. (c),(d) CDDs of Na adsorbed at sites 1 and 6 on the N-MoS_2 substrate. (e),(f) CDDs of Na adsorbed at sites 1 and 6 on the N-MoS_2 (inject e) substrate. For contour plots, the green region represents charge depletion, and the orange region represents charge accumulation. Isosurface value of the CDDs is $0.002 \text{ e}/\text{\AA}^3$.

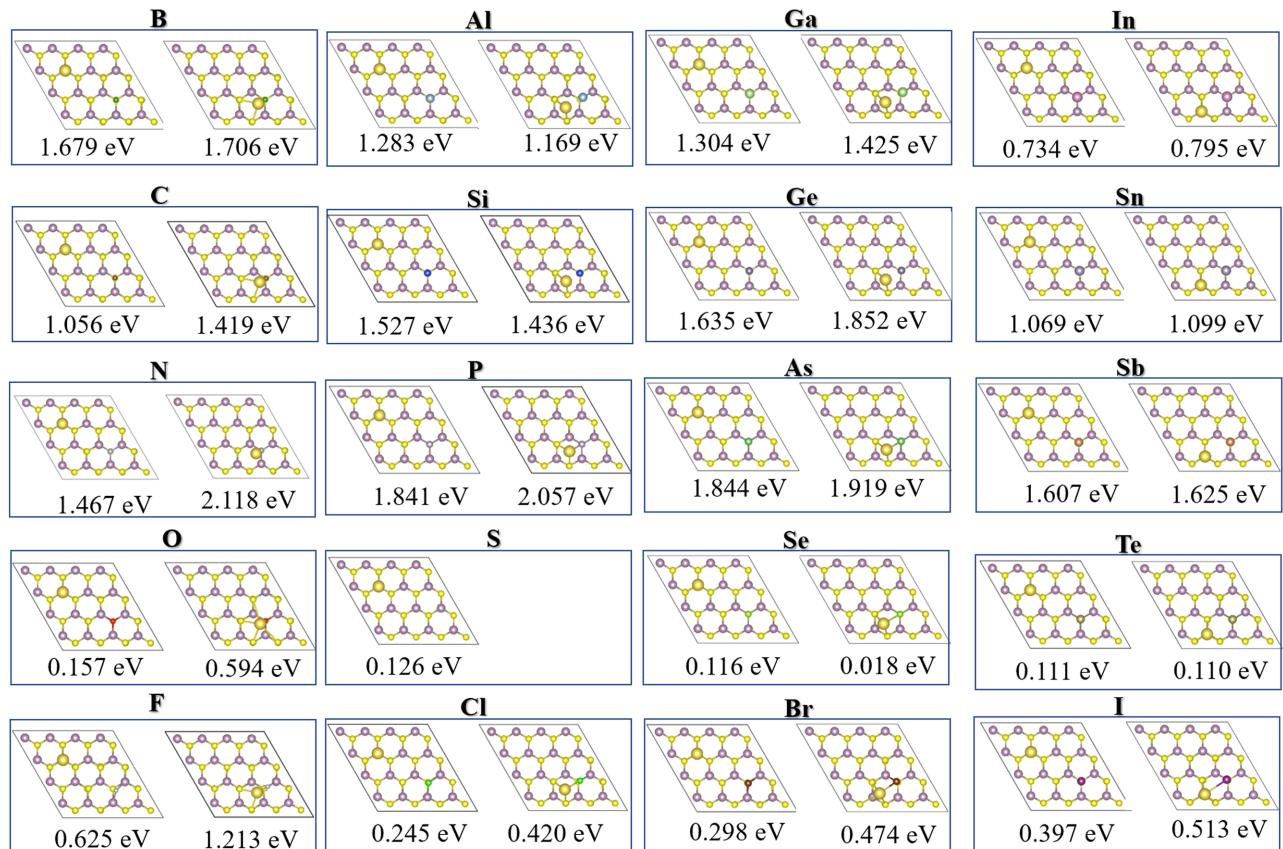


FIG. 8. Optimized structures of $X\text{-MoS}_2$ ($X = \text{B}, \text{Al}, \text{Ga}, \text{In}, \text{C}, \text{Si}, \text{Ge}, \text{Sn}, \text{N}, \text{P}, \text{As}, \text{Sb}, \text{O}, \text{Se}, \text{Te}, \text{F}, \text{Cl}, \text{Br}, \text{I}$) for different dopant elements and the corresponding adsorption energies of Na.

TABLE II. The adsorption energy of Na at site 1 and site 6 on the X -MoS₂ substrate ($X = \text{B}, \text{Al}, \text{Ga}, \text{In}, \text{C}, \text{Si}, \text{Ge}, \text{Sn}, \text{N}, \text{P}, \text{As}, \text{Sb}, \text{O}, \text{Se}, \text{Te}, \text{F}, \text{Cl}, \text{Br}, \text{I}$).

Element	E_{ads} (eV)			E_{ads} (eV)										
	Site 1	Site 6	Ele	Site 1	Site 6									
B	1.68	1.71	C	1.06	1.42	N	1.47	2.12	O	0.16	0.59	F	0.63	1.21
Al	1.28	1.17	Si	1.53	1.44	P	1.84	2.06	S	0.13	0.13	Cl	0.25	0.42
Ga	1.30	1.43	Ge	1.64	1.85	As	1.84	1.92	Se	0.12	0.02	Br	0.30	0.47
In	0.73	0.80	Sn	1.07	1.10	Sb	1.61	1.63	Te	0.11	0.11	I	0.40	0.51

the binding of the dopant atoms on vac-MoS₂ are all exothermic, with binding energies all greater than 2 eV. While the iodine dopant with a binding energy close to 2 eV is reported to exist stably [51], the stability of the X -MoS₂ structures can be inferred.

Tables II and III Figures 7–13.

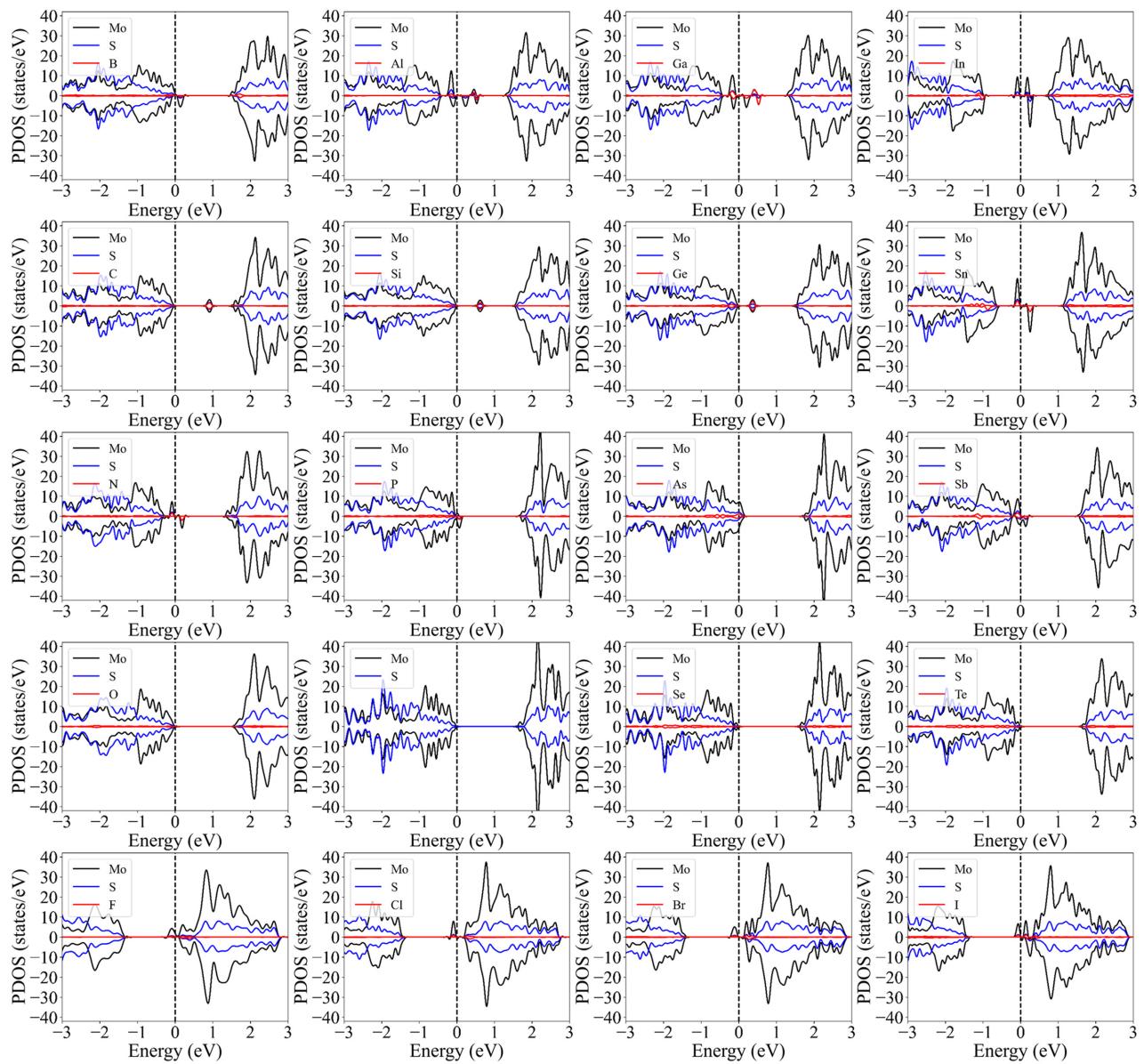


FIG. 9. PDOS of X -MoS₂ ($X = \text{B}, \text{Al}, \text{Ga}, \text{In}, \text{C}, \text{Si}, \text{Ge}, \text{Sn}, \text{N}, \text{P}, \text{As}, \text{Sb}, \text{O}, \text{Se}, \text{Te}, \text{F}, \text{Cl}, \text{Br}, \text{I}$).

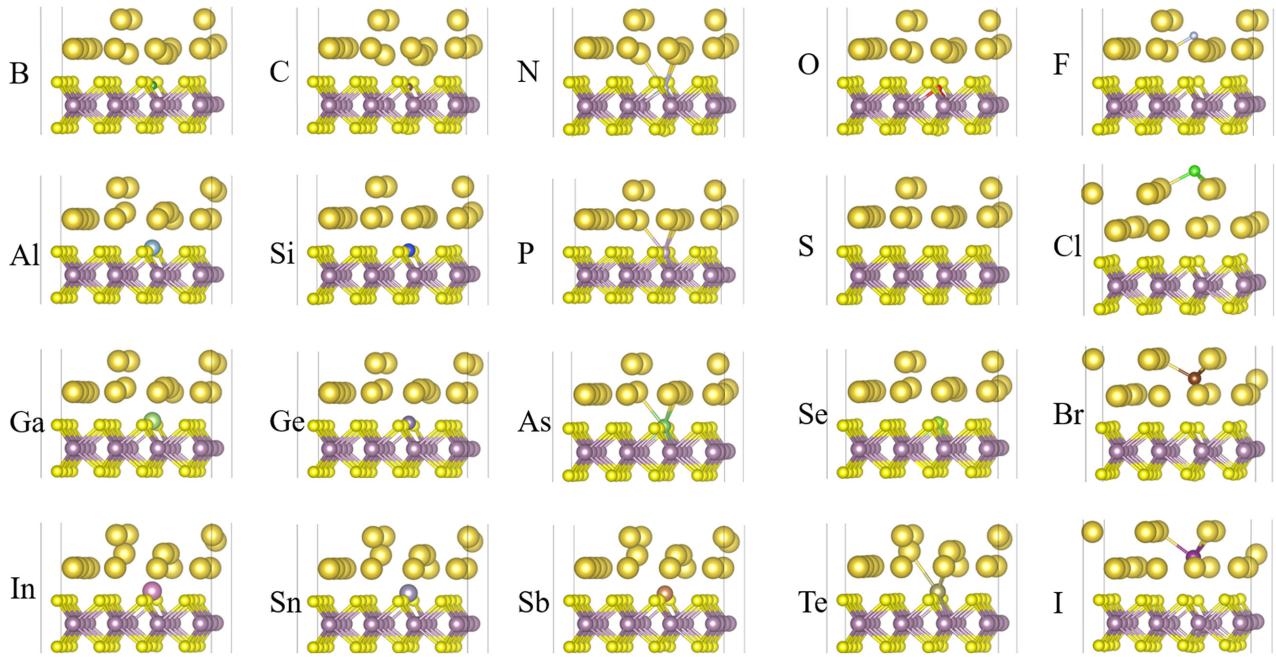


FIG. 10. Multiple Na-adsorption geometries at different sites on $X\text{-MoS}_2$ substrates (X = doped atoms). Here, a concentration of one monolayer of Na atoms is considered, corresponding to a 1:1 ratio of Na:MoS₂.

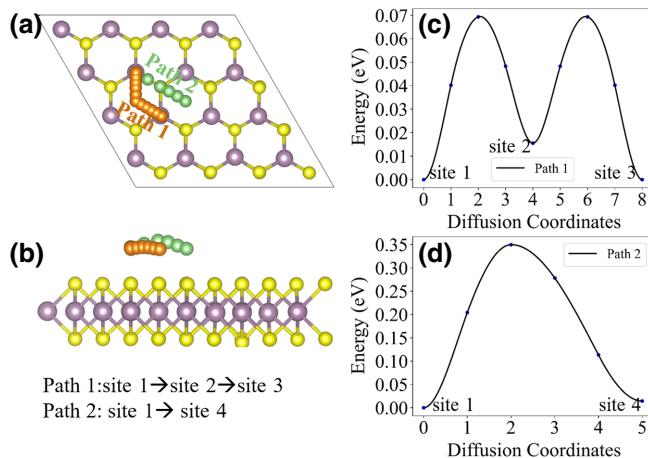


FIG. 11. (a),(b) Top and side views of Na-diffusion path on MoS₂ substrate. (c) Corresponding Na diffusion over the MoS₂ substrate via path 1. (d) Corresponding Na diffusion over the MoS₂ substrate via path 2.

TABLE III. The diffusion barrier of Na on the $X\text{-MoS}_2$ (X = B, Al, Ga, C, Si, Ge, N, P, As) substrate.

Element	Diffusion barrier (eV)	Element	Diffusion barrier (eV)	Element	Diffusion barrier (eV)
B	0.18	C	0.42	N	0.68
Al	0.11	Si	0.10	P	0.21
Ga	0.23	Ge	0.20	As	0.10

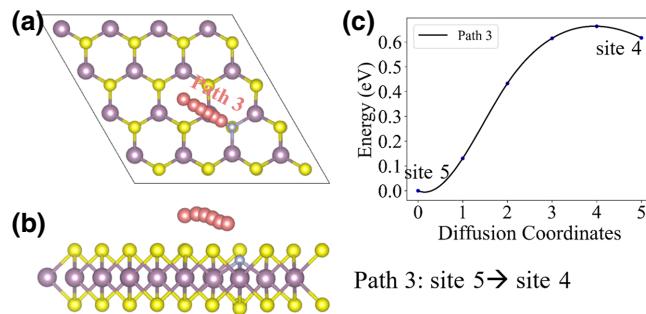


FIG. 12. (a),(b) Top and side views of Na-diffusion path 3 on N-MoS₂ substrate. (c) Corresponding Na diffusion over the N-MoS₂ substrate via path 3.

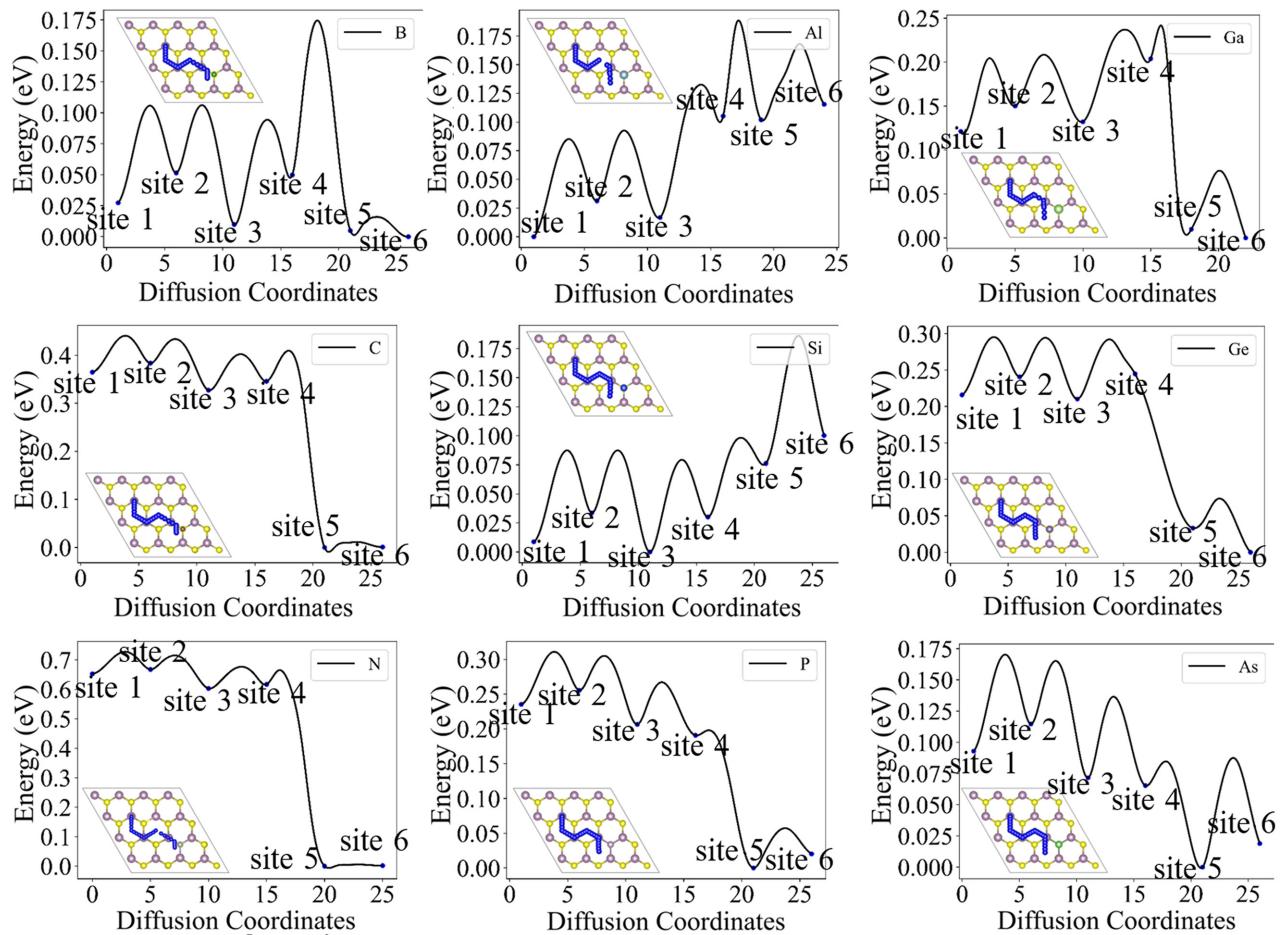


FIG. 13. Diffusion of Na on the $X\text{-MoS}_2$ ($X = \text{B}, \text{Al}, \text{Ga}, \text{C}, \text{Si}, \text{Ge}, \text{N}, \text{P}, \text{As}$) substrate.

TABLE IV. The binding energy of the X atom adsorbed on vac-MoS₂ ($X = \text{doped atoms}$).

Element	E_{bind} (eV)	Ele	E_{bind} (eV)								
Li	2.72	B	5.32	C	6.99	N	6.02	O	7.369	F	4.38
Na	2.49	Al	2.74	Si	4.01	P	4.43	S	6.08	Cl	3.11
Mg	1.77	Ga	2.20	Ge	3.14	As	3.84	Se	8.13	Br	2.55
		In	2.74	Sn	3.44	Sb	3.36	Te	4.45	I	2.01

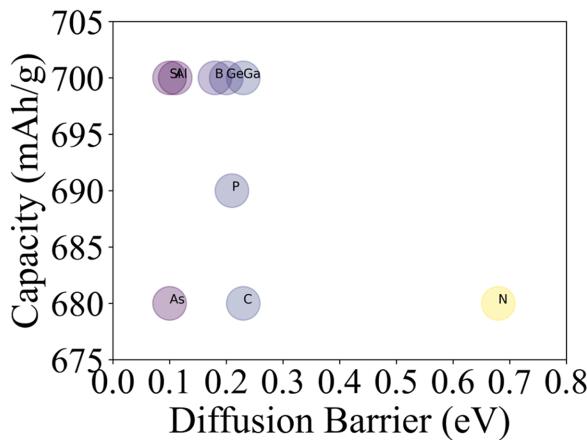


FIG. 14. Relationship between theoretical capacity and barrier.

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